## NSN 5962-01-174-1380

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-174-1380

**Body Length:** 

1.060 inches

**Body Width:** 

Between 0.220 inches and 0.310 inches

**Body Height:** 

0.185 inches

**Maximum Power Dissipation Rating:** 

2.0 watts

**Operating Tempurature Range:** 

-55.0/+125.0 degrees celsius

**Storage Tempurature Range:** 

-65.0/+150.0 degrees celsius

**Features Provided:** 

Hermetically sealed and burn in and monolithic and programmable and bipolar

**Inclosure Material:** 

Ceramic

**Inclosure Configuration:** 

Dual-in-line

**Output Logic Form:** 

Bipolar metal-oxide semiconductor

**Input Circuit Pattern:** 

16 input

**Case Outline Source And Designator:** 

D-8 mil-m-38510

**Current Rating Per Characteristic:** 

100.00 milliamperes reverse current, dc

**Terminal Surface Treatment:** 

Solder

**Voltage Rating And Type Per Characteristic:** 

5.0 volts power source

**Time Rating Per Chacteristic:** 

45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level output

**Memory Device Type:** 

Pal

**Test Data Document:** 

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

**Terminal Type And Quantity:** 

20 printed circuit

**Specification Data:** 

81349-mil-m-38510/503 government specification

Shelf Life:

NI/o

## NSN 5962-01-174-1380

Memory Microcircuit - Page 2 of 2



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Demilitarization:

No

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